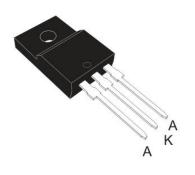
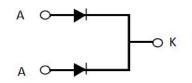


FRED Ultrafast Soft Recovery Diode, 30A

Features:

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low power loss, less RFI and EMI
- Low I_R value
- High surge capacity
- Epitaxial chip construction





Product Summary		
VR	400 V	
lf(AV)	2*15A	
trr	24ns	

Description/Applications

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery behavior of the diodes offers the need as snubber in most applications. These devices are ideally suited for HF welding power converters and other applications where the switching losses are not significant portion of the total losses.

Parameter	Symbol	Test Conditions	Values	Units
Repetitive peak reverse voltage	Vrrm		400	V
Continuous forward current	lf(AV)	Tc =110°C	30	
Single pulse forward current	İfsm	Tc =25°C	180	Α
Maximum repetitive forward current	IFRM	Square wave, 20kHZ	40	
Operating junction	Тј		175	°C
Storage temperatures	Tstg		-55 to +175	°C

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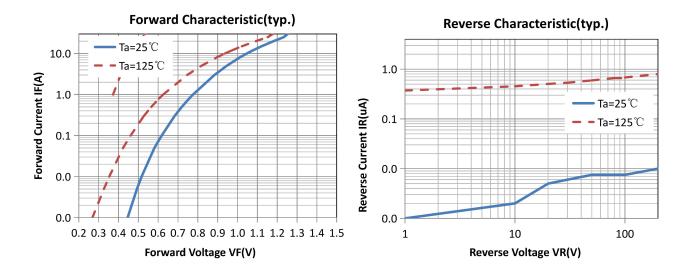


Parameter	Symbol	Test Conditions	Min	Тур.	Max.	Units
Breakdown voltage Blocking voltage	VBR,	Ir=100µA	400			
Forward voltage (Per Diode)	V _R	IF=15 A		1.1	1.45	V
		IF=15 A, Tj =125°C		1.0	1.30	
Reverse leakage current(Per Diode)		VR= VRRM			10	
	lR	Tj=150°C, V _R =400V			100	μΑ
Reverse recovery time(Per Diode)	trr	I _F =0.5A, I _R =1A, I _{RR} =0.25A		32	40	
		I _F =1A,V _R =30V, di/ <i>dt</i> =200A/us		24	35	ns

Thermal characteristics

Paramter	Symbol	Тур	Units
Junction-to-Case	$R_{ heta JC}$	4.0	°C/W

Electrical performance (typic)

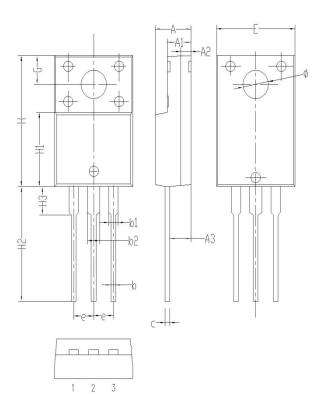


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Package Information

TO-220F PACKAGE



Symbol	Dimensions(millimeters)		
Syllibol	Min.	Max.	
Α	4.30	4.70	
A1	2.80	3.20	
A2	1.10	1.50	
A3	2.50	2.90	
b	0.50	0.75	
b1	1.10	1.35	
b2	1.50	1.75	
С	0.45	0.75	
е	2.34	2.7	
Е	9.85	10.45	
Н	14.8	15.0	
H1	8.30	8.70	
H2	12.7	13.7	
H3	3.10	3.50	
G	2.50	2.90	
ФР	3.10	3.40	

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